

FEATURES

1.8 V to 5.5 V Single Supply
5 Ω (Max) On Resistance
0.75 Ω (Typ) On Resistance Flatness
Automotive Temperature Range: -40°C to $+125^{\circ}\text{C}$
 -3 dB Bandwidth > 200 MHz
Rail-to-Rail Operation
6-Lead SC70 Package
Fast Switching Times:
 $t_{\text{ON}} = 12$ ns
 $t_{\text{OFF}} = 6$ ns
Typical Power Consumption (< 0.01 μW)
TTL/CMOS Compatible

APPLICATIONS

Battery-Powered Systems
Communication Systems
Sample-and-Hold Systems
Audio Signal Routing
Video Switching
Mechanical Reed Relay Replacement

GENERAL DESCRIPTION

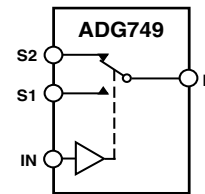
The ADG749 is a monolithic CMOS SPDT switch. This switch is designed on a submicron process that provides low power dissipation yet gives high switching speed, low on resistance, and low leakage currents.

The ADG749 can operate from a single-supply range of 1.8 V to 5.5 V, making it ideal for use in battery-powered instruments and with the new generation of DACs and ADCs from Analog Devices.

Each switch of the ADG749 conducts equally well in both directions when on. The ADG749 exhibits break-before-make switching action.

Because of the advanced submicron process, -3 dB bandwidths of greater than 200 MHz can be achieved.

The ADG749 is available in a 6-lead SC70 package.

FUNCTIONAL BLOCK DIAGRAM

*SWITCHES SHOWN FOR A LOGIC "1" INPUT

PRODUCT HIGHLIGHTS

1. 1.8 V to 5.5 V Single-Supply Operation. The ADG749 offers high performance, including low on resistance and fast switching times, and is fully specified and guaranteed with 3 V and 5 V supply rails.
2. Very Low R_{ON} (5 Ω Max at 5 V and 10 Ω Max at 3 V). At 1.8 V operation, R_{ON} is typically 40 Ω over the temperature range.
3. Automotive Temperature Range: -40°C to 125°C .
4. On Resistance Flatness ($R_{\text{FLAT}(\text{ON})}$) (0.75 Ω typ).
5. -3 dB Bandwidth > 200 MHz.
6. Low Power Dissipation. CMOS construction ensures low power dissipation.
7. Fast $t_{\text{ON}}/t_{\text{OFF}}$.
8. Tiny 6-lead SC70 package.

REV. A

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ADG749—SPECIFICATIONS¹ ($V_{DD} = 5\text{ V} \pm 10\%$, $GND = 0\text{ V}$.)

Parameter	B Version			Unit	Test Conditions/Comments
	25°C	-40°C to +85°C	-40°C to +125°C		
ANALOG SWITCH					
Analog Signal Range			0 V to V_{DD}	V	
On Resistance (R_{ON})	2.5 5	6	7	Ω typ Ω max	$V_S = 0\text{ V}$ to V_{DD} , $I_S = -10\text{ mA}$; Test Circuit 1
On Resistance Match Between Channels (ΔR_{ON})		0.1 0.8	0.8	Ω typ Ω max	$V_S = 0\text{ V}$ to V_{DD} , $I_S = -10\text{ mA}$
On Resistance Flatness ($R_{FLAT(ON)}$)	0.75	1.2	1.5	Ω typ Ω max	$V_S = 0\text{ V}$ to V_{DD} , $I_S = -10\text{ mA}$
LEAKAGE CURRENTS²					
Source Off Leakage I_S (Off)	± 0.01 ± 0.25	± 0.35	1	nA typ nA max	$V_{DD} = 5.5\text{ V}$ $V_S = 4.5\text{ V}/1\text{ V}$, $V_D = 1\text{ V}/4.5\text{ V}$; Test Circuit 2
Channel On Leakage I_D , I_S (On)	± 0.01 ± 0.25	± 0.35	5	nA typ nA max	$V_S = V_D = 1\text{ V}$ or $V_S = V_D = 4.5\text{ V}$; Test Circuit 3
DIGITAL INPUTS					
Input High Voltage, V_{INH}			2.4	V min	
Input Low Voltage, V_{INL}			0.8	V max	
Input Current I_{INL} or I_{INH}	0.005		± 0.1	μA typ μA max	$V_{IN} = V_{INL}$ or V_{INH}
DYNAMIC CHARACTERISTICS²					
t_{ON}	7		12	ns typ ns max	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ $V_S = 3\text{ V}$; Test Circuit 4
t_{OFF}	3		6	ns typ ns max	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ $V_S = 3\text{ V}$; Test Circuit 4
Break-Before-Make Time Delay, t_D	8		1	ns typ ns min	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$, $V_{S1} = V_{S2} = 3\text{ V}$; Test Circuit 5
Off Isolation	-67 -87			dB typ dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 10\text{ MHz}$ $R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$; Test Circuit 6
Channel-to-Channel Crosstalk	-62 -82			dB typ dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 10\text{ MHz}$ $R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$; Test Circuit 7
Bandwidth -3 dB	200			MHz typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$; Test Circuit 8
C_S (OFF)	7			pF typ	
C_D , C_S (ON)	27			pF typ	
POWER REQUIREMENTS					
I_{DD}	0.001		1.0	μA typ μA max	$V_{DD} = 5.5\text{ V}$ Digital Inputs = 0 V or 5.5 V

NOTES

¹Temperature range is as follows: B Version: -40°C to +125°C.

²Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

SPECIFICATIONS¹ (V_{DD} = 3 V ± 10%, GND = 0 V.)

Parameter	B Version			Unit	Test Conditions/Comments
	25°C	-40°C to +85°C	-40°C to +125°C		
ANALOG SWITCH					
Analog Signal Range			0 V to V _{DD}	V	
On Resistance (R _{ON})	6	7	10	Ω typ Ω max	V _S = 0 V to V _{DD} , I _S = -10 mA; Test Circuit 1
On Resistance Match Between Channels (ΔR _{ON})		0.1	0.8	Ω typ Ω max	V _S = 0 V to V _{DD} , I _S = -10 mA
On Resistance Flatness (R _{FLAT(ON)})		2.5	0.8	Ω typ	V _S = 0 V to V _{DD} , I _S = -10 mA
LEAKAGE CURRENTS²					
Source Off Leakage I _S (Off)	±0.01			nA typ	V _{DD} = 3.3 V V _S = 3 V/1 V, V _D = 1 V/3 V; Test Circuit 2
Channel On Leakage I _D , I _S (On)	±0.25	±0.35	1	nA max	
	±0.01			nA typ	V _S = V _D = 1 V or V _S = V _D = 3 V; Test Circuit 3
	±0.25	±0.35	5	nA max	
DIGITAL INPUTS					
Input High Voltage, V _{INH}			2.0	V min	
Input Low Voltage, V _{INL}			0.8	V max	
Input Current I _{INL} or I _{INH}	0.005			μA typ μA max	V _{IN} = V _{INL} or V _{INH}
			±0.1		
DYNAMIC CHARACTERISTICS²					
t _{ON}	10		15	ns typ ns max	R _L = 300 Ω, C _L = 35 pF V _S = 2 V; Test Circuit 4
t _{OFF}	4		8	ns typ ns max	R _L = 300 Ω, C _L = 35 pF V _S = 2 V; Test Circuit 4
Break-Before-Make Time Delay, t _D	8		1	ns typ ns min	R _L = 300 Ω, C _L = 35 pF V _{S1} = V _{S2} = 2 V; Test Circuit 5
Off Isolation	-67			dB typ	R _L = 50 Ω, C _L = 5 pF, f = 10 MHz
	-87			dB typ	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz; Test Circuit 6
Channel-to-Channel Crosstalk	-62			dB typ	R _L = 50 Ω, C _L = 5 pF, f = 10 MHz
	-82			dB typ	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz; Test Circuit 7
Bandwidth -3 dB	200			MHz typ	R _L = 50 Ω, C _L = 5 pF; Test Circuit 8
C _S (Off)	7			pF typ	
C _D , C _S (On)	27			pF typ	
POWER REQUIREMENTS					
I _{DD}	0.001		1.0	μA typ μA max	V _{DD} = 3.3 V Digital Inputs = 0 V or 3.3 V

NOTES

¹Temperature range is as follows: B Version: -40°C to +125°C.

²Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

ABSOLUTE MAXIMUM RATINGS¹

(T_A = 25°C, unless otherwise noted)

V _{DD} to GND	−0.3 V to +7 V
Analog, Digital Inputs ²	−0.3 V to V _{DD} + 0.3 V or 30 mA, Whichever Occurs First
Peak Current, S or D	100 mA (Pulsed at 1 ms, 10% Duty Cycle Max)
Continuous Current, S or D	30 mA
Operating Temperature Range	
Industrial (B Version)	−40°C to +125°C
Storage Temperature Range	−65°C to +150°C
Junction Temperature	150°C
SC70 Package, Power Dissipation	315 mW
θ _{JA} Thermal Impedance	332°C/W
θ _{JC} Thermal Impedance	120°C/W
Lead Temperature, Soldering	
Vapor Phase (60 sec)	215°C
Infrared (15 sec)	220°C
ESD	1.5 kV

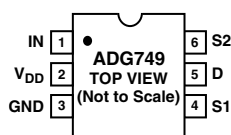
¹Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one absolute maximum rating may be applied at any one time.

²Overvoltages at IN, S, or D will be clamped by internal diodes. Current should be limited to the maximum ratings given.

Table I. Truth Table

ADG749 IN	Switch S1	Switch S2
0	ON	OFF
1	OFF	ON

PIN CONFIGURATION



TERMINOLOGY

V _{DD}	Most Positive Power Supply Potential
GND	Ground (0 V) Reference
S	Source Terminal. May be an input or output.
D	Drain Terminal. May be an input or output.
IN	Logic Control Input
R _{ON}	Ohmic Resistance between D and S
ΔR _{ON}	On Resistance Match between any Two Channels i.e., R _{ON} max – R _{ON} min
R _{FLAT(ON)}	Flatness is defined as the difference between the maximum and minimum value of on resistance as measured over the specified analog signal range.
I _S (Off)	Source Leakage Current with the Switch Off
I _D , I _S (On)	Channel Leakage Current with the Switch On
V _D (V _S)	Analog Voltage on Terminals D and S
C _S (Off)	Off Switch Source Capacitance
C _D , C _S (On)	On Switch Capacitance
t _{ON}	Delay between applying the digital control input and the output switching on.
t _{OFF}	Delay between applying the digital control input and the output switching off.
t _D	Off time or on time measured between the 90% points of both switches, when switching from one address state to another.
Crosstalk	A measure of unwanted signal that is coupled through from one channel to another as a result of parasitic capacitance.
Off Isolation	A measure of unwanted signal coupling through an off switch.
Bandwidth	The frequency at which the output is attenuated by −3 dBs.
On Response	The Frequency Response of the On Switch
Insertion Loss	Loss due to On Resistance of the Switch

ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option	Branding Information*
ADG749BKS	−40°C to +125°C	SC70 (6-Lead Plastic Surface Mount)	KS-6	SHB

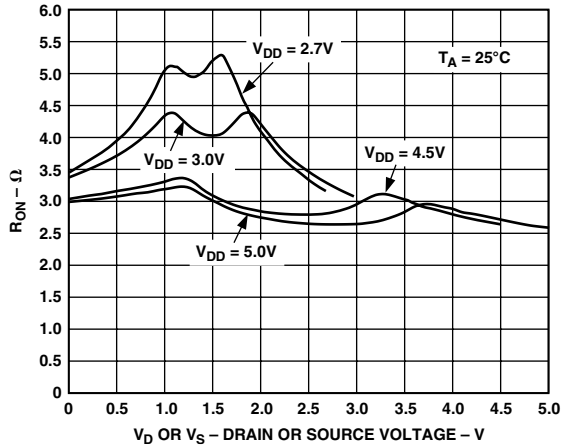
*Branding on this package is limited to three characters due to space constraints.

CAUTION

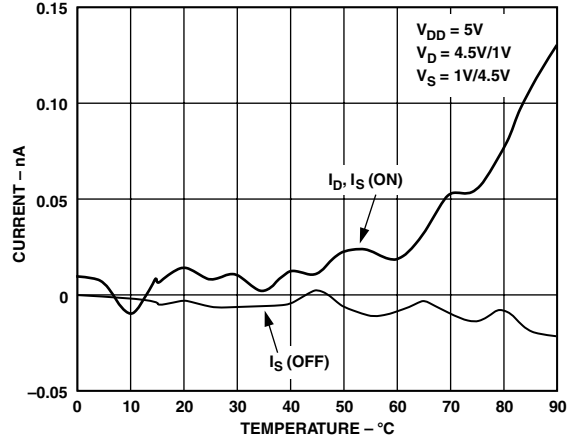
ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the ADG749 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



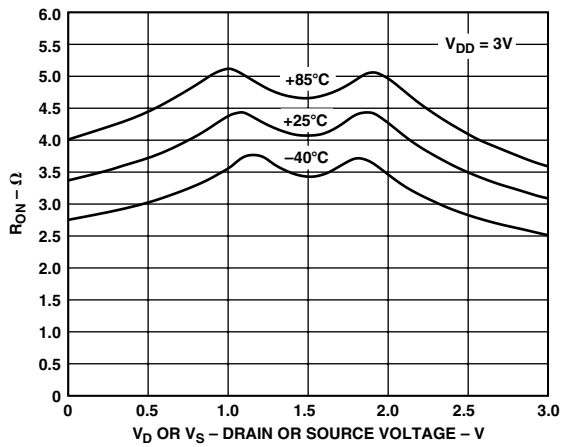
Typical Performance Characteristics—ADG749



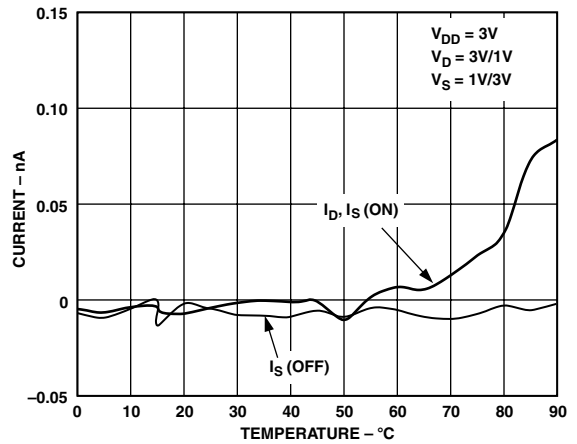
TPC 1. On Resistance vs. V_D (V_S) Single Supplies



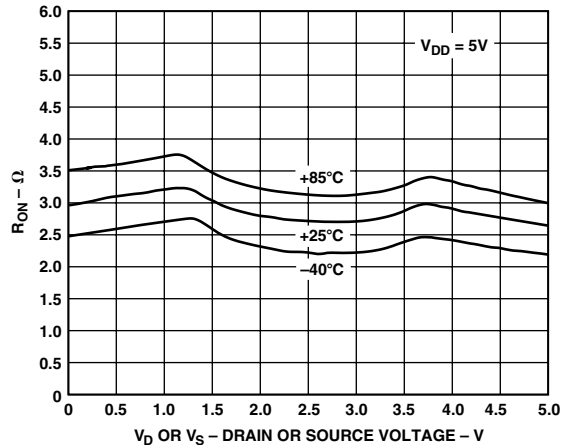
TPC 4. Leakage Currents vs. Temperature



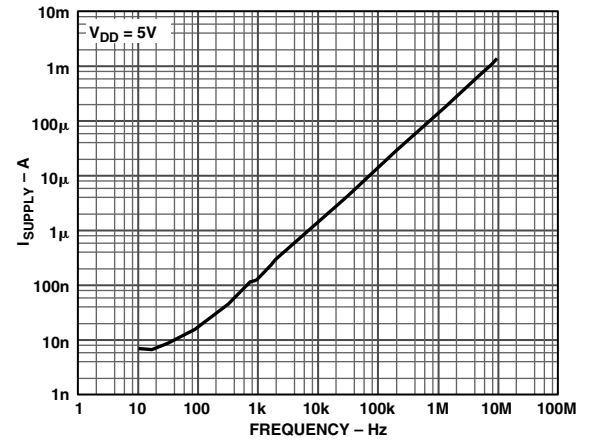
TPC 2. On Resistance vs. V_D (V_S) for Different Temperatures $V_{DD} = 3\text{V}$



TPC 5. Leakage Currents vs. Temperature

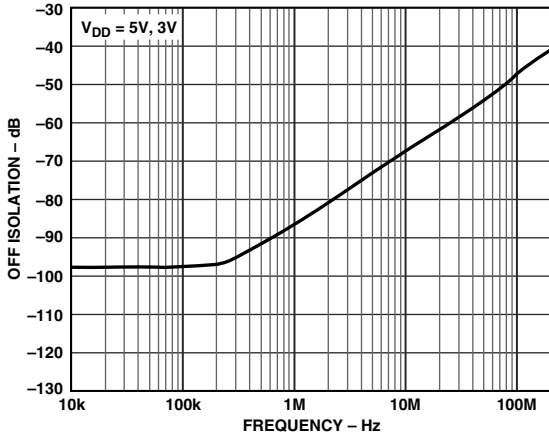


TPC 3. On Resistance vs. V_D (V_S) for Different Temperatures, $V_{DD} = 5\text{V}$

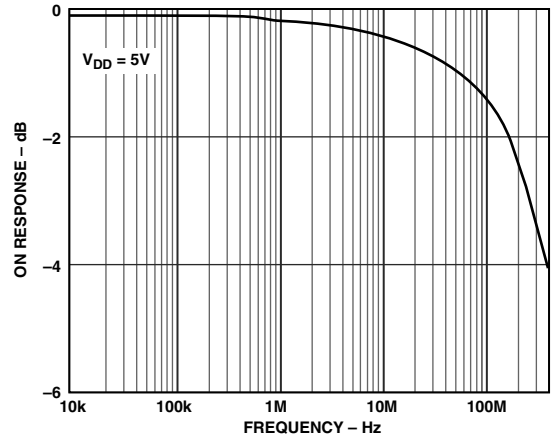


TPC 6. Supply Current vs. Input Switching Frequency

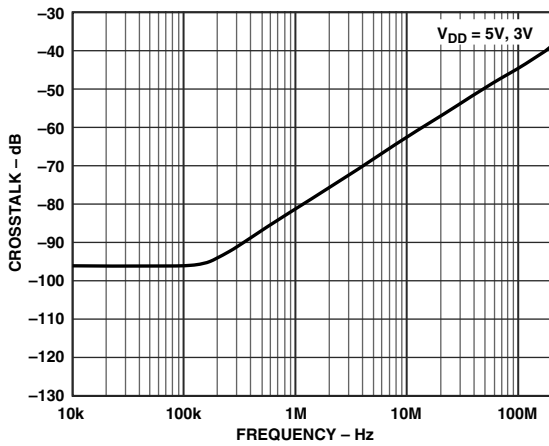
ADG749



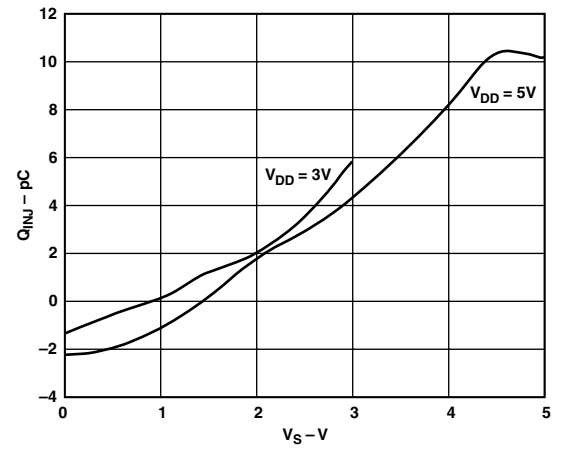
TPC 7. Off Isolation vs. Frequency



TPC 9. On Response vs. Frequency



TPC 8. Crosstalk vs. Frequency



TPC 10. Charge Injection vs. Source Voltage

ADG749

Revision History

Location	Page
7/02—Data Sheet changed from REV. 0 to REV. A.	
Changes to FEATURES	1
Additions to PRODUCT HIGHLIGHTS	1
Changes to SPECIFICATIONS	2
Edits to ABSOLUTE MAXIMUM RATINGS	4
Changes to TERMINOLOGY	4
Edits to ORDERING GUIDE	4
Added new TPCs 4 and 5	5
Added TPC 10	6
TEST CIRCUITS 6, 7, and 8 replaced	7
Updated KS-6 Package Drawing	9

